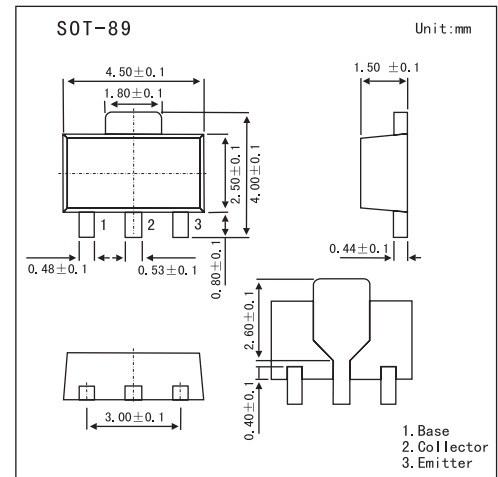


Power Transistor

2SB1260

■ Features

- High breakdown voltage and high current. $BV_{CEO} = -80V$, $I_C = -1A$
- Good hFE linearity.
- Low $V_{CE(sat)}$.
- Epitaxial planar type
- PNP silicon transistor

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-80	V
Collector-emitter voltage	V_{CE0}	-80	V
Emitter-base voltage	V_{EB0}	-5	V
Collector current	I_C	-1	A
Collector current(Pulse)	I_{CP}^*	-2	A
Collector power dissipation	P_C	0.5	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

* Single pulse, $P_w = 100ms$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CB0}	$I_C = -50\mu A$	-80			V
Collector-emitter breakdown voltage	BV_{CE0}	$I_C = -1mA$	-80			V
Emitter-base breakdown voltage	BV_{EB0}	$I_E = -50\mu A$	-5			V
Collector cutoff current	I_{CBO}	$V_{CB} = -60V$			-1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -4V$			-1	μA
Collector-emitter saturation voltage	hFE	$V_{CE} = -3V$, $I_C = -0.1A$	82		390	
DC current transfer ratio	$V_{CE(sat)}$	$I_C = -500mA$, $I_B = -50mA$			-0.4	V
Transition frequency	C_{ob}	$V_{CE} = -5V$, $I_E = 50mA$, $f = 30MHz$		100		MHz
Output capacitance	f_T	$V_{CB} = -10V$, $I_E = 0A$, $f = 1MHz$		25		pF

■ hFE Classification

Marking	BE		
	P	Q	R
hFE	82~180	120~270	180~390